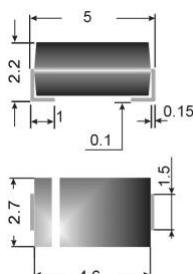


FR 2SMA A ... FR 2SMA M



Surface mount diode

Fast silicon rectifier diodes

FR 2SMA A ... FR 2SMA M

Forward Current: 2 A

Reverse Voltage: 50 to 1000 V

Features

- Max. solder temperature: 260°C
- Plastic material has UL classification 94V-0

Mechanical Data

- Plastic case: SMA / DO-214AC
- Weight approx.: 0,07 g
- Terminals: plated terminals solderable per MIL-STD-750
- Mounting position: any
- Standard packaging: 7500 pieces per reel

1) Max. temperature of the terminals $T_T = 100^\circ\text{C}$

2) $I_F = 2 \text{ A}$, $T_J = 25^\circ\text{C}$

3) $T_A = 25^\circ\text{C}$

4) Mounted on P.C. board with 25 mm² copper pads at each terminal

Type	Polarity color band	Repetitive peak reverse voltage V_{RRM} V	Surge peak reverse voltage V_{RSM} V	Maximum forward voltage $T_j = 25^\circ\text{C}$ $I_F = 2 \text{ A}$ V_F ²⁾ V	Maximum reverse recovery time $I_F = 0,5 \text{ A}$ $I_R = 1 \text{ A}$ $I_{RR} = 0,25 \text{ A}$ t_{rr} ns
FR 2SMA A	-	50	50	1,3	150
FR 2SMA B	-	100	100	1,3	150
FR 2SMA D	-	200	200	1,3	150
FR 2SMA G	-	400	400	1,3	150
FR 2SMA J	-	600	600	1,3	250
FR 2SMA K	-	800	800	1,3	500
FR 2SMA M	-	1000	1000	1,3	500

Absolute Maximum Ratings

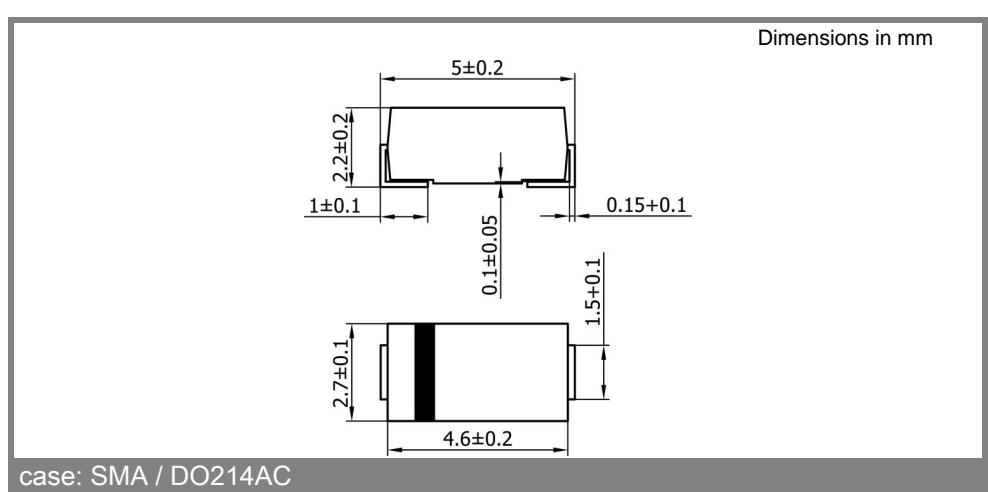
$T_A = 25^\circ\text{C}$, unless otherwise specified

Symbol	Conditions	Values	Units
$I_{F\text{AV}}$	Max. averaged fwd. current, R-load, $T_T = 100^\circ\text{C}$ ¹⁾	2	A
$I_{F\text{RM}}$	Repetitive peak forward current $f > 15 \text{ Hz}$ ¹⁾	10	A
$I_{F\text{SM}}$	Peak fwd. surge current 50 Hz half sinus-wave ³⁾	50	A
$I_{\text{f}t}$	Rating for fusing, $t < 10 \text{ ms}$ ³⁾	12,5	A ² s
R_{thA}	Max. thermal resistance junction to ambient ⁴⁾	70	K/W
R_{thT}	Max. thermal resistance junction to terminals	30	K/W
T_j	Operating junction temperature	- 50 ... + 150	°C
T_s	Storage temperature	- 50 ... + 150	°C

Characteristics

$T_A = 25^\circ\text{C}$, unless otherwise specified

Symbol	Conditions	Values	Units
I_R	Maximum leakage current, $T_j = 25^\circ\text{C}$; $V_R = V_{RRM}$ $T_j = 100^\circ\text{C}$; $V_R = V_{RRM}$	<5 <200	µA µA
C_J	Typical junction capacitance (at MHz and applied reverse voltage of V)	-	pF
Q_{rr}	Reverse recovery charge ($U_R = V$; $I_F = A$; $dI_F/dt = A/\text{ms}$)	-	µC
E_{RSM}	Non repetitive peak reverse avalanche energy ($I_R = mA$; $T_j = ^\circ\text{C}$; inductive load switched off)	-	mJ



FR 2SMA A ... FR 2SMA M

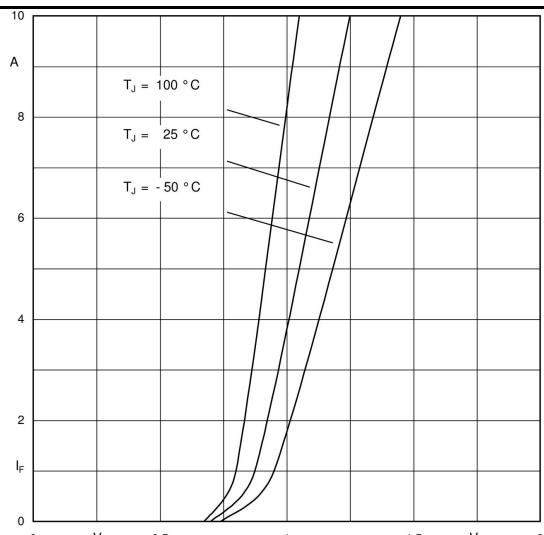


Fig. 1 Forward characteristics (typical values)

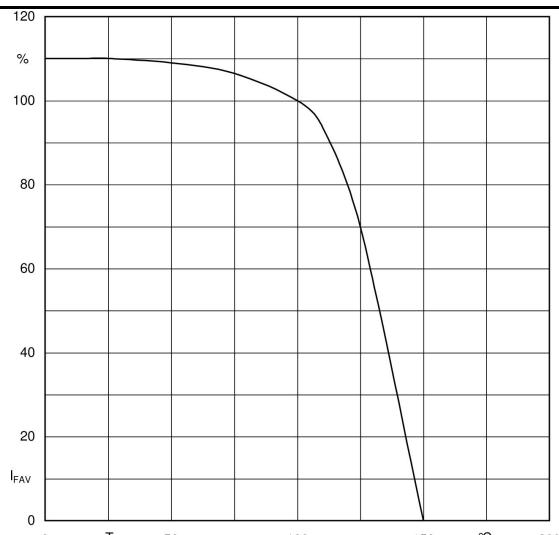


Fig. 2 Rated forward current vs. temp. of the terminals⁴⁾